YJ Planar Fast Recovery Diode Die Specification

400V 5A, Fast recovery diode die based on silicon planar process

Part No.: FRD05A400AS-290A

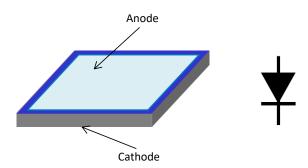
Main Products Characterstics

• Average forward current: IF(AV) = 5A

• Maximum operating junction temperature: Tj = 150 °C

Planar Construction

· Top metal: Al



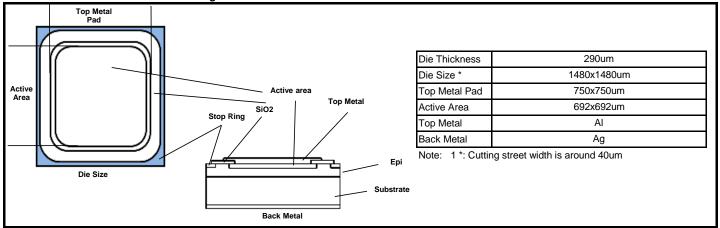
Maximum Ratings

Parameter	Symbol	Rating			
Repetitive peak reverse voltage	V_{RRM}	400V			
Average forward current	I _{F(AV)}	5A			
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	50A			
Storage temperature range	T _{stg}	-40 to +150 °C			
Maximum operating junction temperature	T _j	150 °C			

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
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Reverse breakdown voltage $I_R = 50uA$	V_{BR}	420V	440V
Maximum forward voltage drop I_F = 5A, Pulse Test: tp = 380 $\mu s,~\delta \leqslant 2\%$	V _F	1.25V	1.22V
Reverse Recovery Time I _F =0.5A, I _R =1A, I _{rr} =0.25A	Trr	35ns	28ns
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: tp = 10 ms, $\delta \leqslant 2\%$	I _R	2uA	0.02uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangite Electronics does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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